

Ka-Band High Power Reflective SPDT PIN Switch 26-40 GHz

Rev. V2

Features

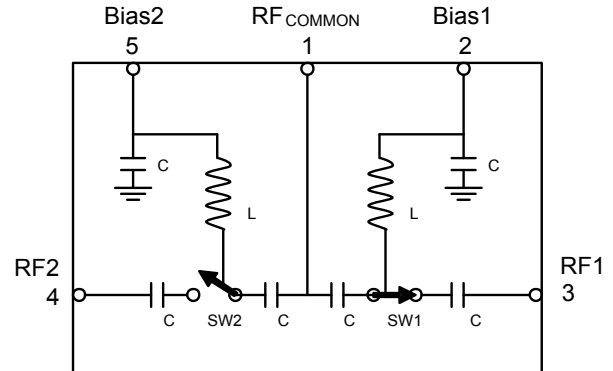
- Broadband Performance, 26 to 40 GHz
- Low Loss: 0.6 dB
- High Isolation: 32 dB
- Up to 13 W CW Power, +85°C
- Die with G-S-G RF Pads and DC Bias Pads
- Includes DC Blocks and RF Bias Networks

Description and Applications

The MASW-010646 is a high power SPDT. This broadband, reflective, high linearity, SPDT switch was developed for Ka-Band applications that require up to 13 W of power handling while maintaining low insertion loss and high isolation.

The SPDT MMIC utilizes MACOM's proven AlGaAs PIN diode technology. The switch is fully passivated with silicon nitride and has an added polymer layer for scratch protection. The protective coating prevents damage to the junction and the anode air-bridge during handling and assembly. The die has backside metallization to facilitate an epoxy die attach process.

Functional Diagram



Pin Configuration:

(Back Metal is RF, D.C., and Thermal Ground)

Pin	Function
1	RF _{COMMON}
2	BIAS 1
3	RF1
4	RF2
5	BIAS 2

Ordering Information¹

Part Number	Package
MASW-010646-13940G	Die in Gel Pack

1. Die quantity varies.

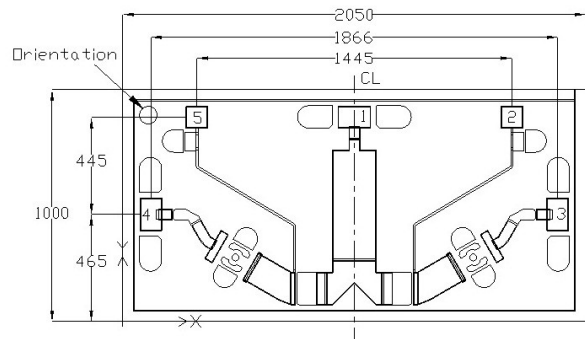
Handling Procedures

Please observe the following precautions to avoid damage:

Static Sensitivity

Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these HBM class 1A devices.

Die Outline



Dimensions indicated in μm .
 Die Thickness : 100 μm
 RF Pads (1, 3 & 4) are 100 x 150 μm .
 DC Bias Pads (2 & 5) are 100 x 100 μm .
 Meets JEDEC moisture sensitivity level 1 requirements.

¹ * Restrictions on Hazardous Substances, European Union Directive 2002/95/EC.

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Electrical Specifications: Freq. = 28 - 38 GHz, $T_A = +25^\circ\text{C}$, +25 mA, -15 V, $Z_0 = 50 \Omega$

Parameter	Test Conditions	Units	Min.	Typ.	Max.
Insertion Loss	26 GHz	dB	—	0.60	—
	28 GHz			0.60	0.90
	35 GHz			0.60	0.90
	38 GHz			0.60	0.90
	40 GHz			0.70	—
Isolation ²	26 GHz	dB	—	34	—
	28 GHz		29	35	
	35 GHz		33	39	
	38 GHz		35	41	
	40 GHz		—	42	
RF _{COMMON} Return Loss, On state	26 GHz	dB	—	16	—
	28 GHz			18	
	35 GHz			16	
	38 GHz			16	
	40 GHz			16	
RF1, RF2 Return Loss, On state	26 GHz	dB	—	16	—
	28 GHz			18	
	35 GHz			16	
	38 GHz			16	
	40 GHz			16	
Switching Speed-Ton	50% DC to 90% RF	ns	—	25	—
Switching Speed-Toff	50% DC to 10% RF	ns	—	23	—
Rise Time -Tr	10% to 90% RF	ns	—	9	—
Fall Time - Tf	90% to 10% RF	ns	—	9	—
CW Input Power ³	-25 V	dBm	—	41.2	—
Reverse Bias Voltage ³	—	V	-32	-15	-5
Reverse Bias Current ³	-15 V	nA	—	25	—

2. Isolation defined with 1 port in low loss state.

3. Reverse bias voltage should be determined based on working conditions. For example, -25 V @ 41.2 dBm input power. For lower power applications, a less negative voltage can be used.

Absolute Maximum Ratings^{4,5}

Parameter	Absolute Maximum
Negative DC Bias Voltage	-50 V
DC Forward Bias Current	40 mA
CW Incident Power	43 dBm
Operating Temperature	-40°C to +85°C
Storage Temperature	-65°C to +150°C

4. Exceeding any one or combination of these limits may cause permanent damage to this device.

5. MACOM does not recommend sustained operation near these survivability limits.

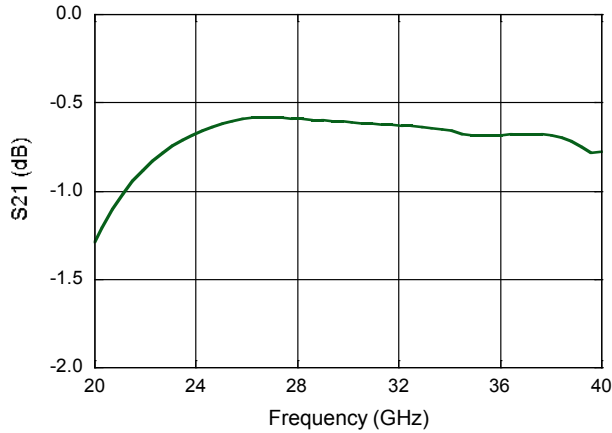
Truth Table⁶

RF _{COMMON} Path	Bias 1	Bias 2
RF1 Insertion Loss RF2 Isolation	-15 V	25 mA
RF2 Insertion Loss RF1 Isolation	25 mA	-15 V

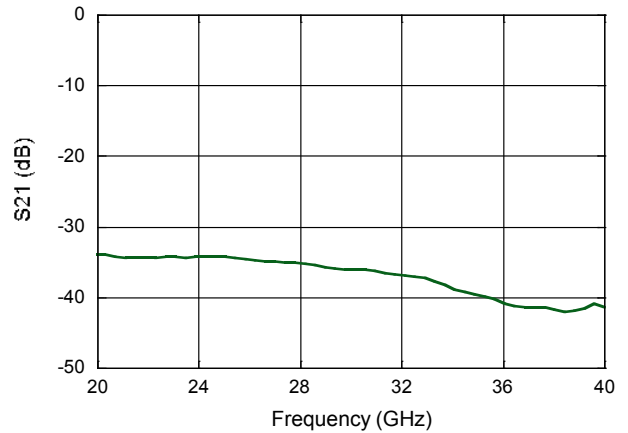
6. R. Caverly and G. Hiller, "Establishing the Minimum Reverse Bias for a PIN Diode in a High Power Switch," IEEE Transactions on Microwave Theory and Techniques, Vol.38, No.12, December 1990.

Typical Performance: $T_A = +25^\circ\text{C}$, $+25\text{ mA}$, -15 V , $Z_0 = 50\ \Omega$

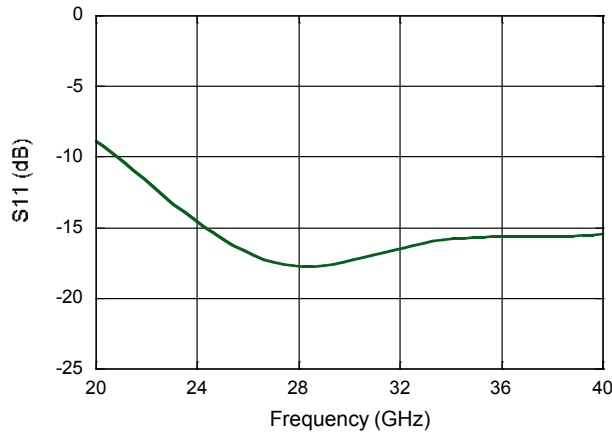
Insertion Loss (On State)



Isolation (Off State)



RF_{COMMON} Return Loss ((On State)



RF_{1, 2} Return Loss (On State)

